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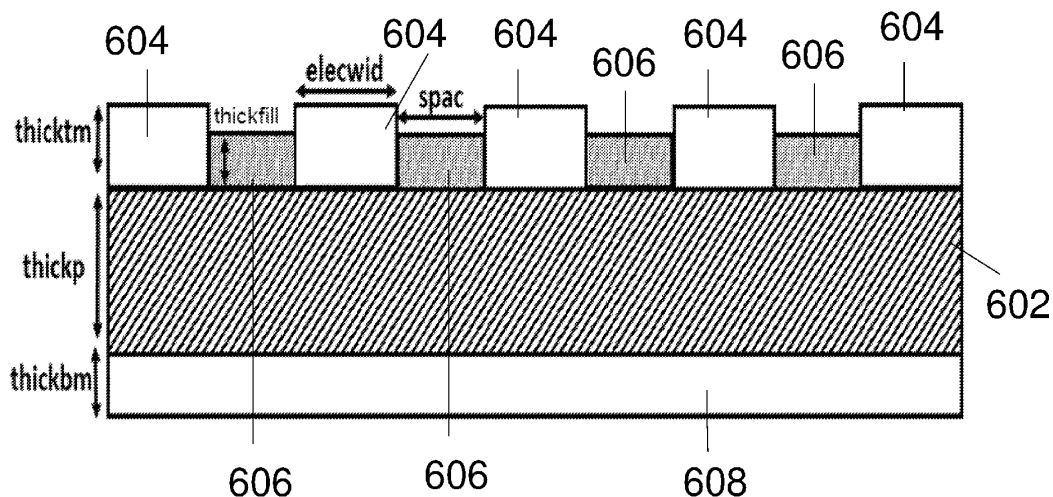
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(54) Title: ACOUSTIC RESONATOR AND METHOD OF FORMING THE SAME

FIG. 6A



(57) Abstract: Various embodiments may relate to an acoustic resonator. The acoustic resonator may include a piezoelectric layer. The acoustic resonator may also include a first electrode in contact with a first surface of the piezoelectric layer. The acoustic resonator may further include a plurality of dielectric structures in contact with the first surface of the piezoelectric layer. The acoustic resonator may additionally include a second electrode in contact with a second surface of the piezoelectric layer opposite the first surface. The first electrode may include a plurality of electrode structures. A dielectric structure of the plurality of dielectric structures may be in contact with a pair of neighboring electrode structures of the plurality of electrode structures.

[Continued on next page]

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